

FRED

$$\begin{aligned} V_{RRM} &= 600 \text{ V} \\ I_{FAV} &= 2 \times 150 \text{ A} \\ t_{rr} &= 35 \text{ ns} \end{aligned}$$

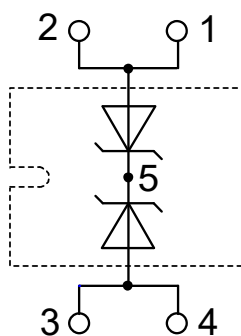
Fast Recovery Epitaxial Diode
 Extreme Low Loss and Soft Recovery
 Common Cathode

Part number

DSEK300-06A



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227UI (minibloc)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

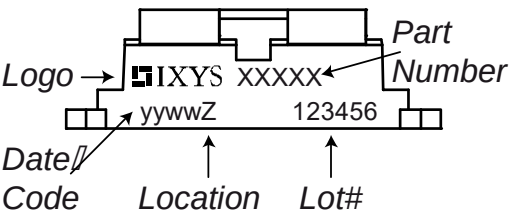
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Fast Diode				Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				600	V	
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				600	V	
I_R	reverse current, drain current	$V_R = 600\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			3	mA	
		$V_R = 480\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			30	mA	
V_F	forward voltage drop	$I_F = 150\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1,17	V	
		$I_F = 300\text{ A}$				1,40	V	
		$I_F = 150\text{ A}$	$T_{VJ} = 150^{\circ}\text{C}$			1,02	V	
		$I_F = 300\text{ A}$				1,36	V	
I_{FAV}	average forward current	$T_C = 110^{\circ}\text{C}$ rectangular d = 0.5	$T_{VJ} = 150^{\circ}\text{C}$			150	A	
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		0,74	V	
r_F	slope resistance					1,25	mΩ	
R_{thJC}	thermal resistance junction to case					0,2	K/W	
R_{thCH}	thermal resistance case to heatsink				0,1		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			625	W	
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; $V_R = 0\text{ V}$		$T_{VJ} = 45^{\circ}\text{C}$		2,00	kA	
C_J	junction capacitance	$V_R = 400\text{ V}$ f = 1 MHz		$T_{VJ} = 25^{\circ}\text{C}$		214	pF	
I_{RM}	max. reverse recovery current	} $I_F = 150\text{ A}; V_R = 300\text{ V}$ -di _F /dt = 600 A/μs		$T_{VJ} = 25^{\circ}\text{C}$		25	A	
				$T_{VJ} = 125^{\circ}\text{C}$		50	A	
t_{rr}	reverse recovery time			$T_{VJ} = 25^{\circ}\text{C}$		60	ns	
				$T_{VJ} = 125^{\circ}\text{C}$		180	ns	

Package SOT-227UI (minibloc)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			200	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				30		g
M_D	mounting torque		1,1		1,5	Nm
M_T	terminal torque		1,1		1,5	Nm

Product Marking

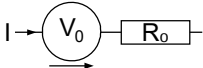


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEK300-06A	DSEK300-06A	Tube	10	517508

Equivalent Circuits for Simulation

* on die level

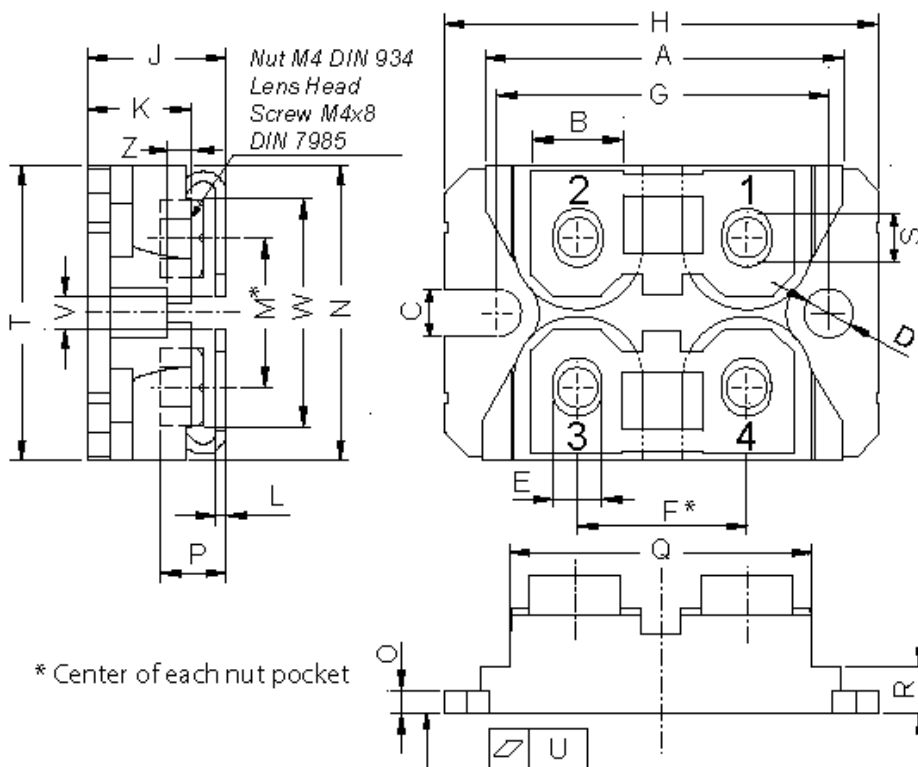
$T_{VJ} = 150^{\circ}C$



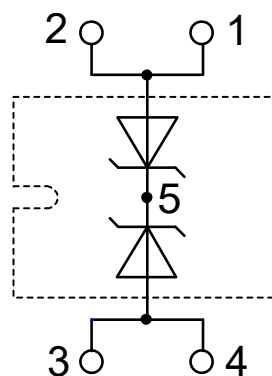
Fast Diode

$V_{0\ max}$
threshold voltage
0,74
V

$R_{0\ max}$
slope resistance *
0,75
mΩ

Outlines SOT-227UI (minibloc)


Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106



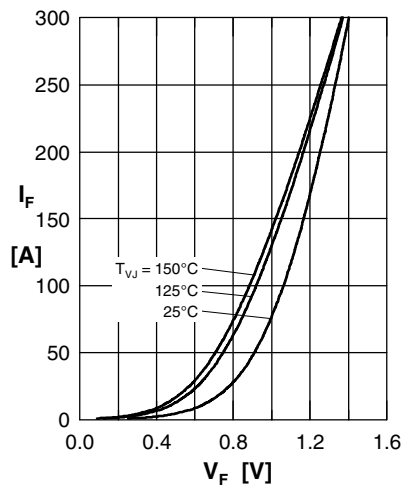
Fast Diode


Fig. 1 Forward current
 I_F versus V_F

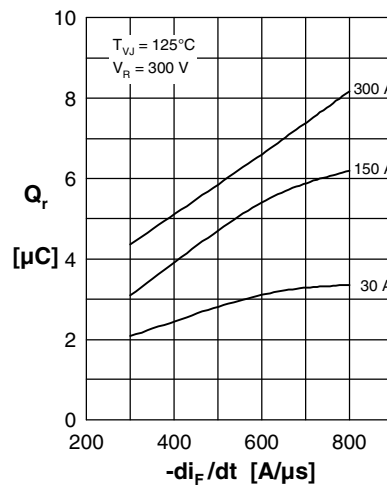


Fig. 2 Typ. reverse recov. charge
 Q_r versus $-di_F/dt$

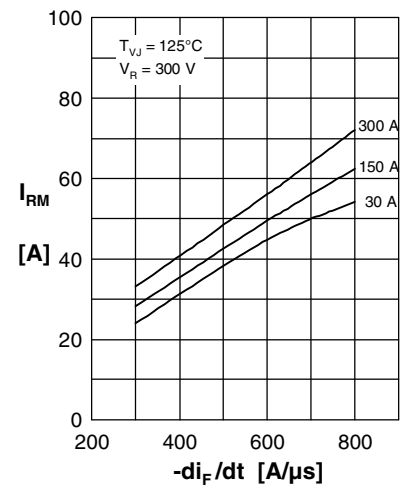


Fig. 3 Typ. peak reverse current
 I_{RM} versus $-di_F/dt$

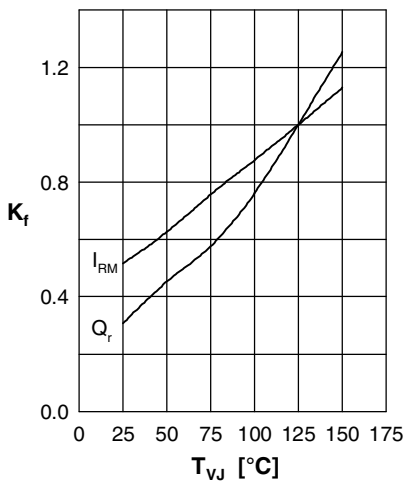


Fig. 4 Typ. dynamic parameters
 Q_r , I_{RM} versus T_{VJ}

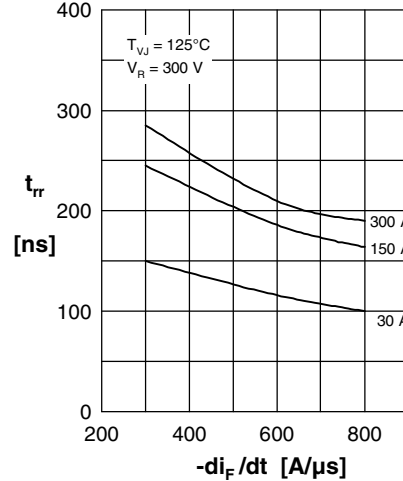


Fig. 5 Typ. recovery time
 t_{rr} versus $-di_F/dt$

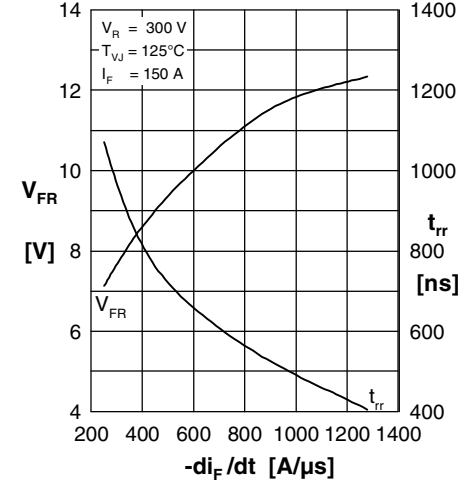


Fig. 6 Typ. peak forward voltage
 V_{FR} and t_{rr} versus $-di_F/dt$

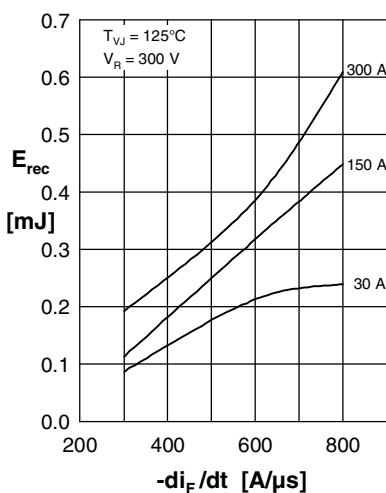


Fig. 7 Typ. recovery energy
 E_{rec} versus $-di_F/dt$

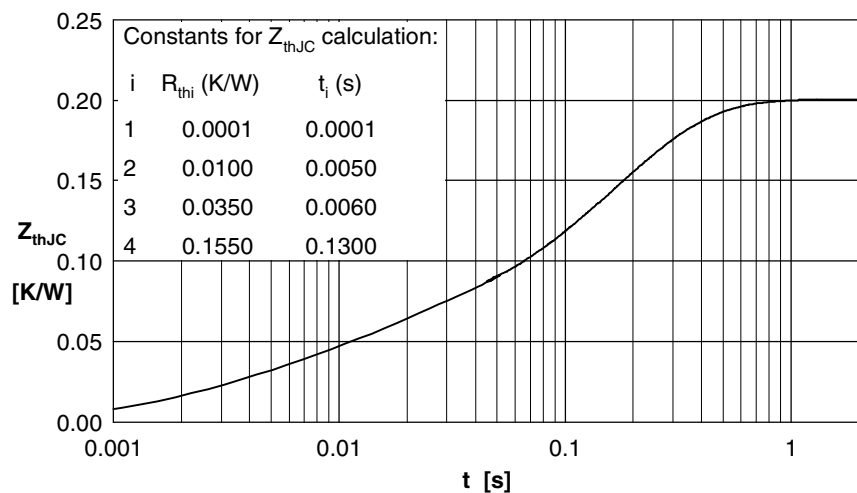


Fig. 8 Transient thermal resistance junction to case